

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC3710A

HIGH CURRENT SWITCHING APPLICATIONS

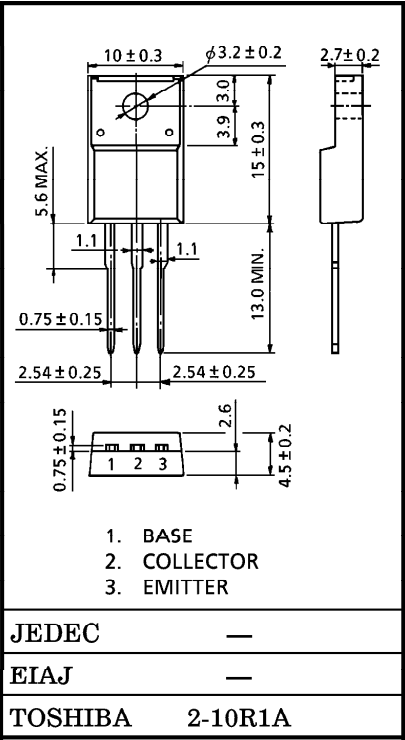
- Low Collector Saturation Voltage : $V_{CE(sat)}=0.4V$ (Max.)
- High Speed Switching Time : $t_{stg}=1.0\mu s$ (Typ.)
- Complementary to 2SA1452A

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	12	A
Base Current	I_B	2	A
Collector Power Dissipation (Tc=25°C)	P_C	30	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

INDUSTRIAL APPLICATIONS

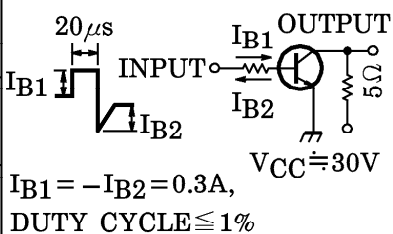
Unit in mm



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 80V, I_E = 0$	—	—	10	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 6V, I_C = 0$	—	—	10	μA
Collector-Emitter Breakdown Voltage		$V_{(BR) CEO}$	$I_C = 50mA, I_B = 0$	80	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)		$V_{CE} = 1V, I_C = 1A$	70	—	240	
	$h_{FE(2)}$		$V_{CE} = 1V, I_C = 6A$	40	—	—	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 6A, I_B = 0.3A$	—	0.2	0.4	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 6A, I_B = 0.3A$	—	0.9	1.2	V
Transition Frequency		f_T	$V_{CE} = 5V, I_C = 1A$	—	80	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	220	—	pF
Switching Time	Turn-on Time	t_{on}	 <p>$I_{B1} = -I_{B2} = 0.3A$, DUTY CYCLE $\leq 1\%$</p>	—	0.2	—	μs
	Storage Time	t_{stg}		—	1.0	—	
	Fall Time	t_f		—	0.2	—	

(Note) $h_{FE(1)}$ Classification O : 70~140, Y : 120~240

